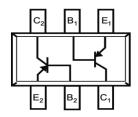
Dual PNP Small Signal Surface Mount Transistor





Features:

- Epitaxial planar die construction.
- · Ideal for low power amplification and switching.
- · Ultra-small surface mount package
- · Also available in lead free version.



SOT-363

Application:

· General switching and amplification

Maximum Rating @ TA = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-40	V
Collector-Emitter Voltage	VCEO	-40	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current -Continuous	Ic	-0.2	А
Total Power Dissipation	Ptot	-0.2	W
Thermal Resistance Junction to Ambient	RθjA	625	°C/W
Storage Temperature	Tstg	150	°C
Junction Temperature	Tj	-55 to -150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Conditions	Min.	Max.	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=-10μA,I _E =0	-40		V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=-1mA,I _B =0	-40		V
Emitter-base breakdown voltage	V(BR)EBO	Iε=-10μA,Ic=0	-5		V
Collector cut-off current	ICEX	Vce=-30V,Veb(off)=-3V	-	-0.05	μA
Base cut-off current	lвь	Vce=-30V,Veb(off)=-3V	-	-0.05	μA
DC current gain	hFE	VcE =-1V,lc= -0.1mA VcE =-1V,lc =-1mA VcE =-1V,lc =-10mA VcE =-1V,lc =-50mA VcE =-1V,lc =-100mA	60 80 100 60 30	- 300 - -	
Collector-emitter saturation voltage	VCE(sat)	Ic =-10mA,Iв =-1mA Ic =-50mA,Iв =-5mA	-	-250 -400	mV mV
Base-emitter saturation voltage	V _{BE} (sat)	Ic =-10mA,Iв =-1mA Ic =-50mA, Iв =-5mA	-650 -	-850 -950	mV mV

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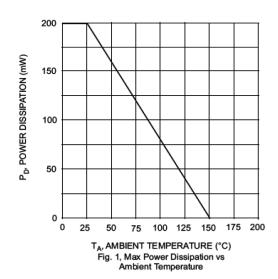


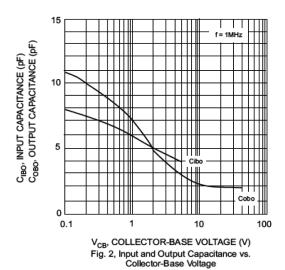
Dual PNP Small SignalSurface Mount Transistor

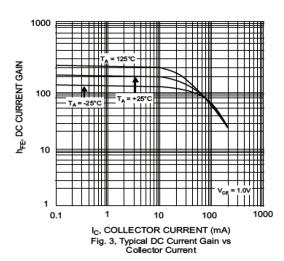


Parameter	Symbol	Conditions	Min.	Max.	Unit
Output Capacitance	Cobo	IE =0,V _{CB} =-5V; f =1MHz	-	4.5	pF
Input Capacitance	Cibo	Ic=0, V _{EВ} =-0.5V; f =1МНz	-	10	pF
Transition Frequency	f⊤	Ic=-1mA,Vc==-10V,f=1KHz	250	-	MHz
Noise Figure	NF	Ic=-0.1mA,Vc==-20V,f=100MHz	-	4	dB
Delay Time	td	Vcc=-3V,VBE(OFF)=0.5V Ic=-10mA	-	35	ns
Rise Time	tr	IB1=-IB2=-1mA	-	35	ns
Storage Time	t s	Vcc=-3V,Ic=-10mA	-	225	ns
Fall Time	tf	IB1=-IB2=-1mA	-	75	ns

Typical Characteristics @ TA = 25°C unless otherwise specified







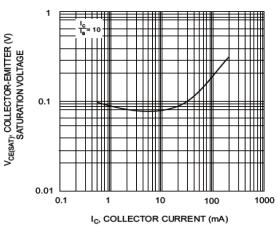


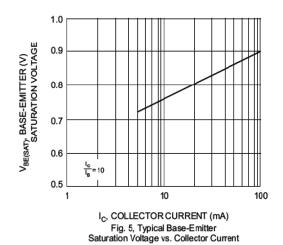
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

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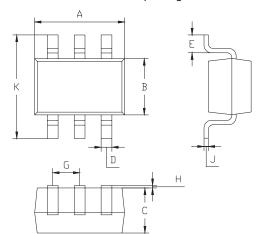
Dual PNP Small Signal Surface Mount Transistor





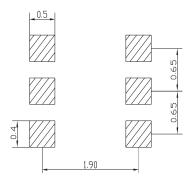
Package Outline

Plastic surface mounted package



SOT-363			
Dim.	Min.	Max.	
Α	1.8	2.2	
В	1.15	1.35	
С	1 Typical		
D	0.1	0.3	
Е	0.25	0.4	
G	0.65 Typical		
Н	0.02	0.1	
J	0.1 Typical		
K	2.1	2.3	
All Dimensions in mm			

Soldering Footprint



Dimensions: Millimetres

Part Number Table

Description	Part Number	
Transistor, Dual PNP, -40V, -200mA, SOT-363	MMDT3906-7-F	

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